

ESD8351, SZESD8351

ESD Protection Diodes

Low Capacitance ESD Protection Diode for High Speed Data Line

The ESD8351 Series ESD protection diodes are designed to protect high speed data lines from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines.

Features

- Low Capacitance (0.55 pF Max, I/O to GND)
- Protection for the Following IEC Standards:
IEC 61000-4-2 (Level 4)
ISO 10605
- Low ESD Clamping Voltage
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- USB 2.0
- eSATA

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	T _L	260	°C
IEC 61000-4-2 Contact (ESD)	ESD	±15	kV
IEC 61000-4-2 Air (ESD)	ESD	±15	kV
ISO 10605 330 pF / 2 kΩ Contact	ESD	±30	kV
Maximum Peak Pulse Current 8/20 μs @ T _A = 25°C	I _{pp}	5.0	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

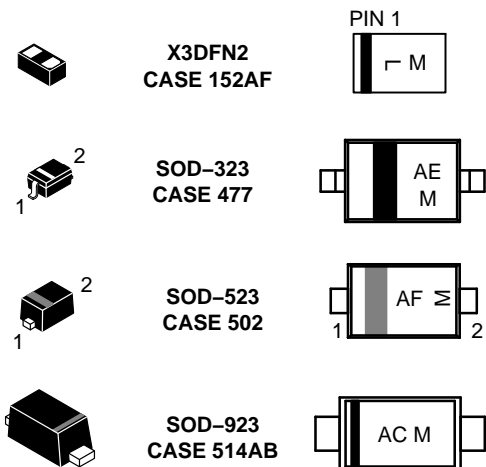
See Application Note AND8308/D for further description of survivability specs.



ON Semiconductor®

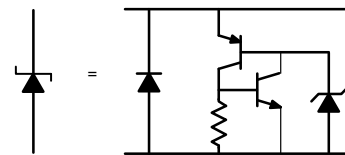
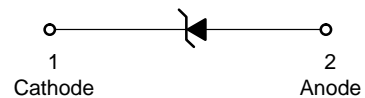
www.onsemi.com

MARKING DIAGRAMS



X, XX = Specific Device Code
M = Date Code

PIN CONFIGURATION AND SCHEMATIC



ORDERING INFORMATION

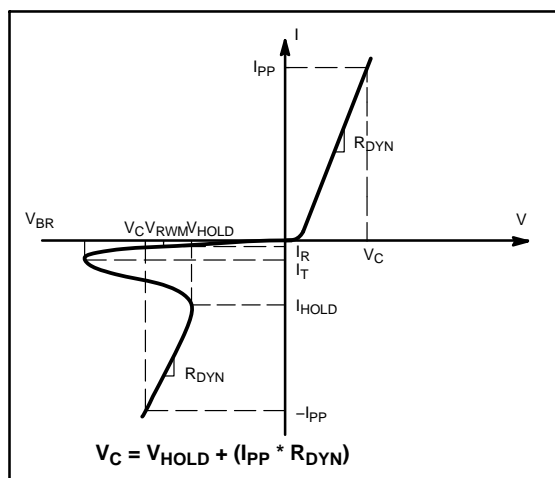
See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

ESD8351, SZESD8351

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
V _{RWM}	Working Peak Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
V _{HOLD}	Holding Reverse Voltage
I _{HOLD}	Holding Reverse Current
R _{DYN}	Dynamic Resistance
I _{PP}	Maximum Peak Pulse Current
V _C	Clamping Voltage @ I _{PP} V _C = V _{HOLD} + (I _{PP} * R _{DYN})



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Working Voltage	V _{RWM}	I/O Pin to GND			3.3	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, I/O Pin to GND	5.5	7.0	7.8	V
Reverse Leakage Current	I _R	V _{RWM} = 3.3 V, I/O Pin to GND			500	nA
Holding Reverse Voltage	V _{HOLD}	I/O Pin to GND		1.15		V
Holding Reverse Current	I _{HOLD}	I/O Pin to GND		20		mA
Clamping Voltage TLP (Note 2) See Figures 1 through 11	V _C	I _{PP} = 8 A } IEC 61000-4-2 Level 2 equivalent (±4 kV Contact, ±4 kV Air)		6.5		V
		I _{PP} = 16 A } IEC 61000-4-2 Level 4 equivalent (±8 kV Contact, ±15 kV Air)		11.2		V
Clamping Voltage (Note 3)	V _C	I _{PP} = 5 A } t _p = 8 x 20 μs		8.2		V
Dynamic Resistance	R _{DYN}	Pin1 to Pin2 Pin2 to Pin1		0.62 0.59		Ω
Junction Capacitance	C _J	V _R = 0 V, f = 1 Mhz V _R = 0 V, f = 2.5 Ghz		0.37 0.35	0.55 0.45	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- For test procedure see Figures 8 and 9 and application note AND8307/D.
- ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model.
TLP conditions: Z₀ = 50 Ω, t_p = 100 ns, t_r = 4 ns, averaging window; t₁ = 30 ns to t₂ = 60 ns.
- Non-repetitive current pulse at T_A = 20°C, per IEC 61000-4-5 waveform.

ESD8351, SZESD8351

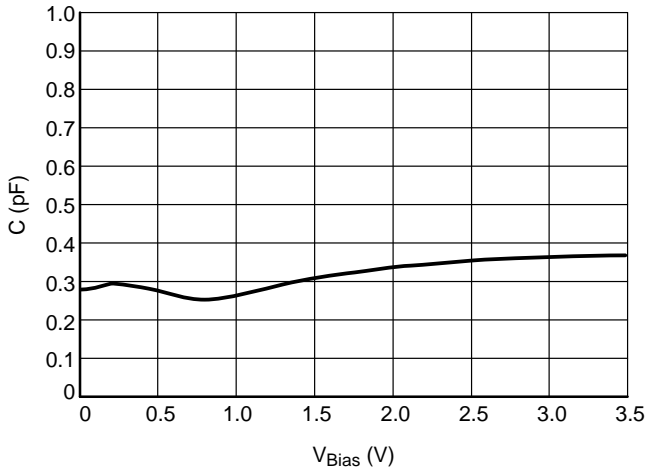


Figure 1. CV Characteristics

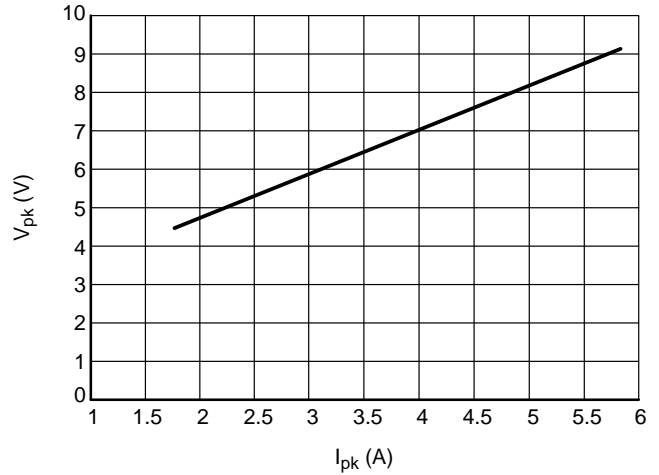


Figure 2. Clamping Voltage vs Peak Pulse Current ($t_p = 8/20 \mu s$)

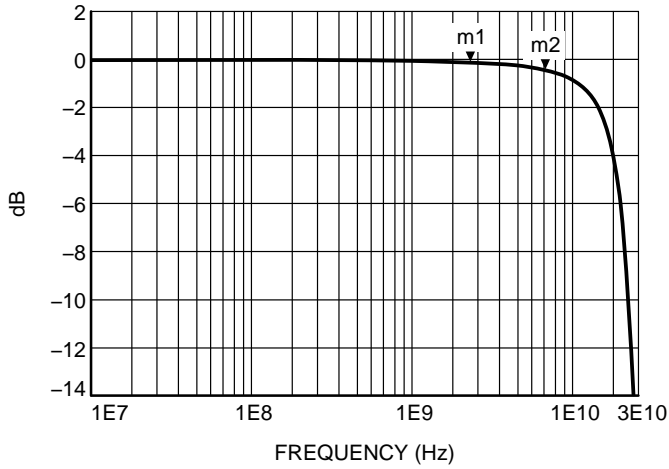


Figure 3. RF Insertion Loss

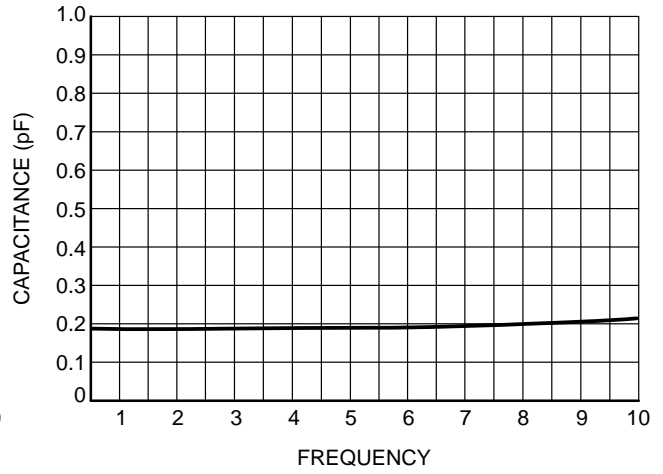


Figure 4. Capacitance over Frequency

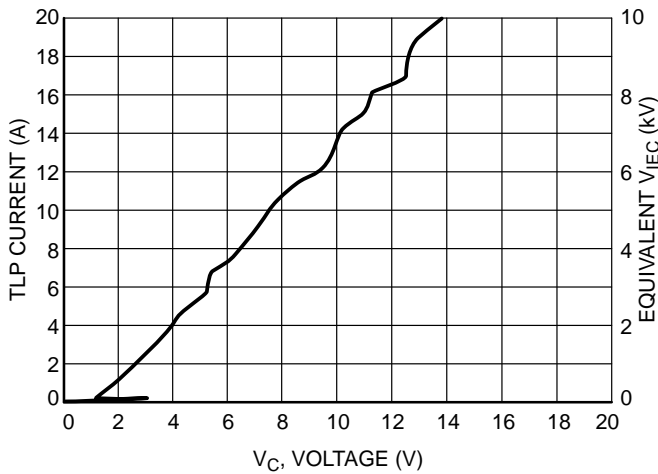


Figure 5. Positive TLP I-V Curve

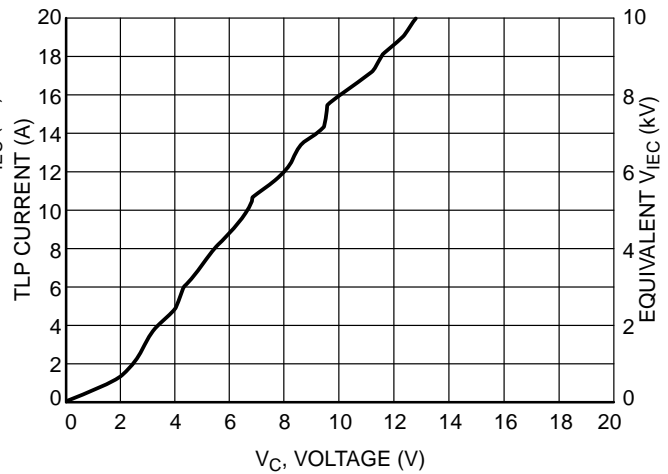


Figure 6. Negative TLP I-V Curve

ESD8351, SZESD8351

Latch-Up Considerations

ON Semiconductor's 8000 series of ESD protection devices utilize a snap-back, SCR type structure. By using this technology, the potential for a latch-up condition was taken into account by performing load line analysis of common high speed serial interfaces. Example load lines for latch-up free applications and applications with the potential for latch-up are shown below with a generic IV characteristic of a snapback, SCR type structured device overlaid on each. In the latch-up free load line case, the IV characteristic of the snapback protection device intersects the load-line in one unique point (V_{OP} , I_{OP}). This is the only

stable operating point of the circuit and the system is therefore latch-up free. In the non-latch up free load line case, the IV characteristic of the snapback protection device intersects the load-line in two points (V_{OPA} , I_{OPA}) and (V_{OPB} , I_{OPB}). Therefore in this case, the potential for latch-up exists if the system settles at (V_{OPB} , I_{OPB}) after a transient. Because of this, ESD8351 Series should not be used for HDMI applications – ESD8104 or ESD8040 have been designed to be acceptable for HDMI applications without latch-up. Please refer to Application Note AND9116/D for a more in-depth explanation of latch-up considerations using ESD8000 series devices.

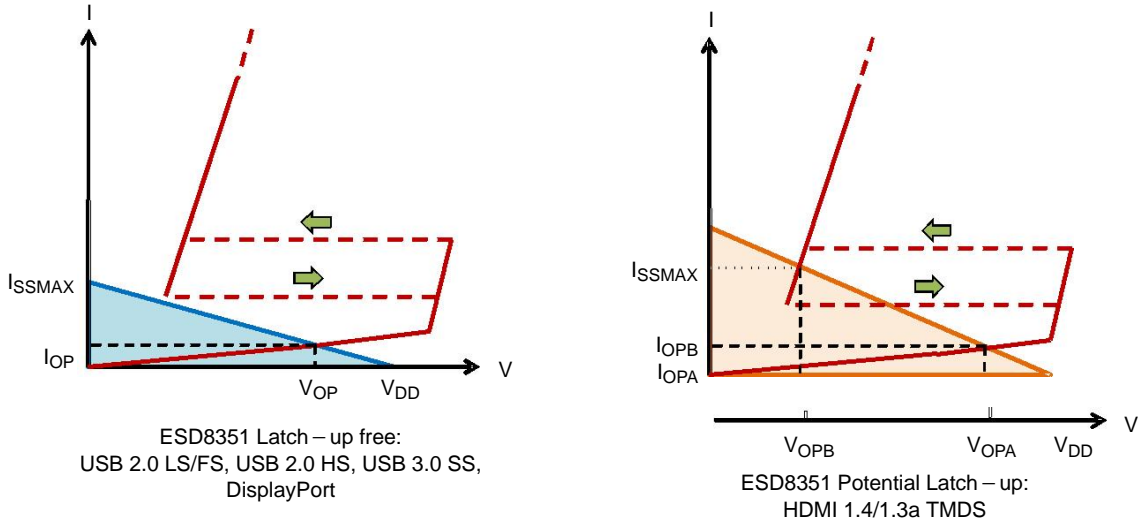


Figure 7. Example Load Lines for Latch-up Free Applications and Applications with the Potential for Latch-up

Table 1. SUMMARY OF SCR REQUIREMENTS FOR LATCH-UP FREE APPLICATIONS

Application	VBR (min) (V)	IH (min) (mA)	VH (min) (V)	ON Semiconductor ESD8000 Series Recommended PN
HDMI 1.4/1.3a TMDS	3.465	54.78	1.0	ESD8104, ESD8040
USB 2.0 LS/FS	3.301	1.76	1.0	ESD8004, ESD8351
USB 2.0 HS	0.482	N/A	1.0	ESD8004, ESD8351
USB 3.0 SS	2.800	N/A	1.0	ESD8004, ESD8006, ESD8351
DisplayPort	3.600	25.00	1.0	ESD8004, ESD8006, ESD8351

ESD8351, SZESD8351

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

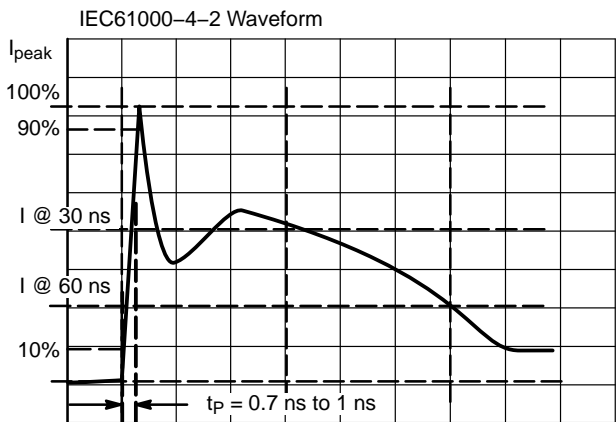


Figure 8. IEC61000-4-2 Spec

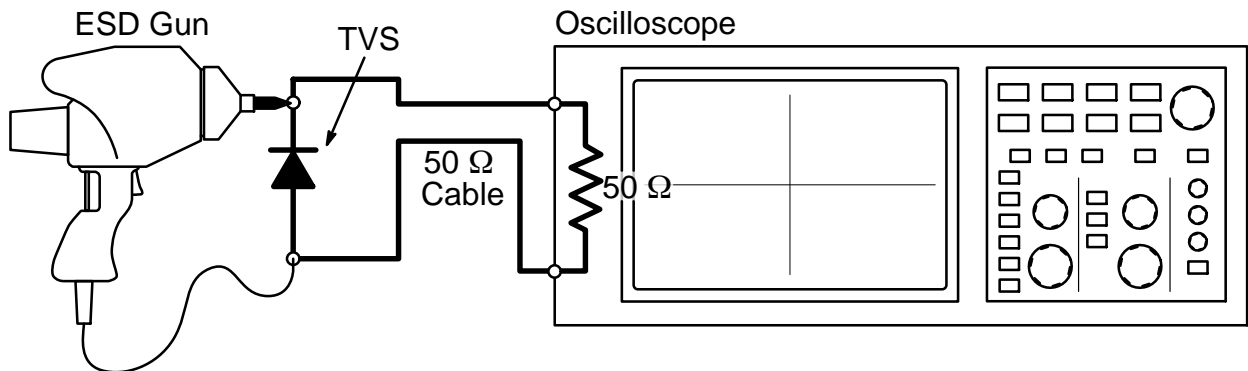


Figure 9. Diagram of ESD Clamping Voltage Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

ESD8351, SZESD8351

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 10. TLP I–V curves of ESD protection devices accurately demonstrate the product’s ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 11 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

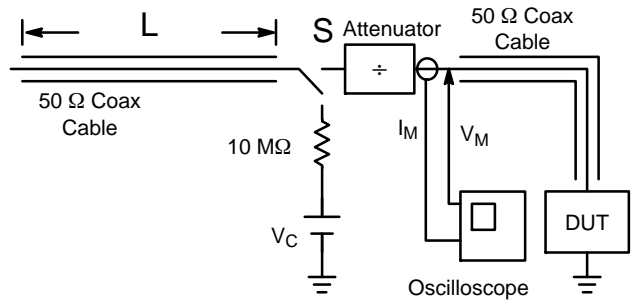


Figure 10. Simplified Schematic of a Typical TLP System

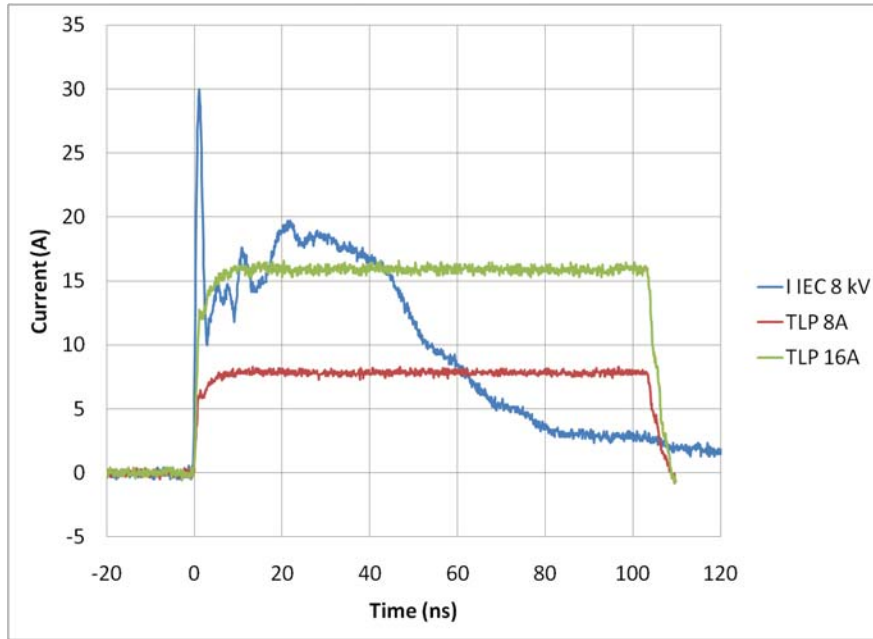


Figure 11. Comparison Between 8 kV IEC 61000–4–2 and 8 A and 16 A TLP Waveforms

ORDERING INFORMATION

Device	Package	Shipping†
ESD8351HT1G, SZESD8351HT1G*	SOD–323 (Pb–Free)	3000 / Tape & Reel
ESD8351XV2T1G, SZESD8351XV2T1G*	SOD–523 (Pb–Free)	3000 / Tape & Reel
ESD8351P2T5G, SZESD8351P2T5G*	SOD–923 (Pb–Free)	8000 / Tape & Reel
ESD8351MUT5G, SZESD8351MUT5G*	X3DFN2 (Pb–Free)	15000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

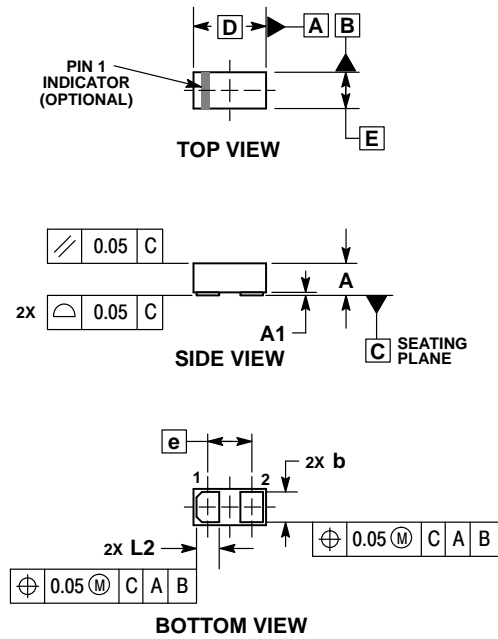
ESD8351, SZESD8351

PACKAGE DIMENSIONS

X3DFN2, 0.62x0.32, 0.355P, (0201)

CASE 152AF

ISSUE A

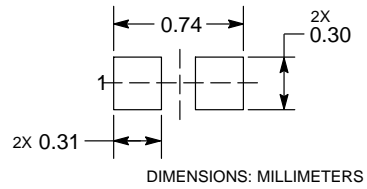


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS		
DIM	MIN	MAX
A	0.25	0.33
A1	---	0.05
b	0.22	0.28
D	0.58	0.66
E	0.28	0.36
e	0.355 BSC	
L2	0.17	0.23

RECOMMENDED MOUNTING FOOTPRINT*

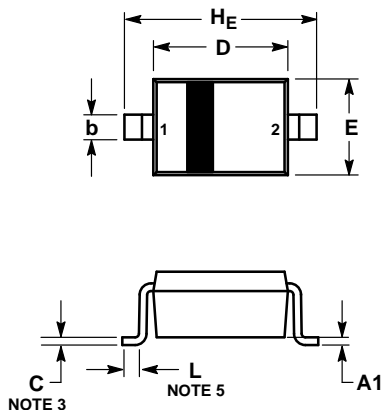


See Application Note AND8398/D for more mounting details
 *For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ESD8351, SZESD8351

PACKAGE DIMENSIONS

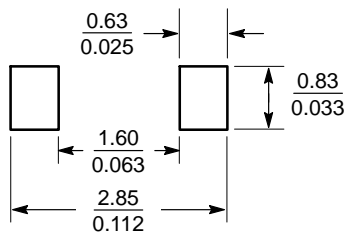
SOD-323
CASE 477-02
ISSUE H



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 5. DIMENSION L IS MEASURED FROM END OF RADIUS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.30	2.50	2.70	0.090	0.098	0.105

SOLDERING FOOTPRINT*

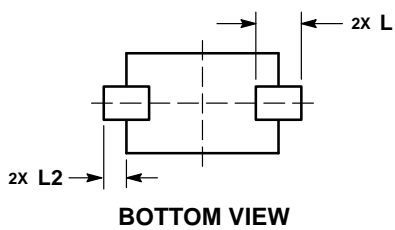
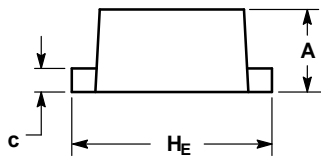
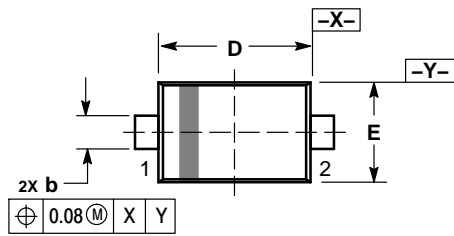


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ESD8351, SZESD8351

PACKAGE DIMENSIONS

SOD-523
CASE 502
ISSUE E

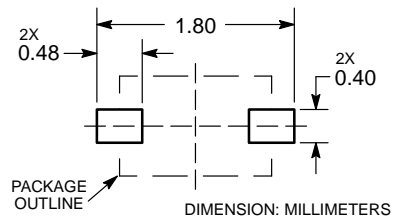


NOTES:

6. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
7. CONTROLLING DIMENSION: MILLIMETERS.
8. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
9. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.50	0.60	0.70
b	0.25	0.30	0.35
c	0.07	0.14	0.20
D	1.10	1.20	1.30
E	0.70	0.80	0.90
H E	1.50	1.60	1.70
L	0.30 REF		
L2	0.15	0.20	0.25

**RECOMMENDED
SOLDERING FOOTPRINT***

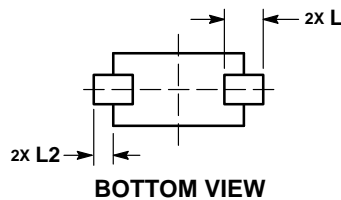
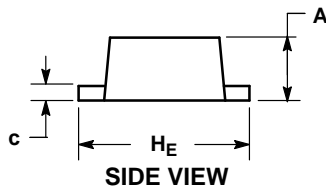
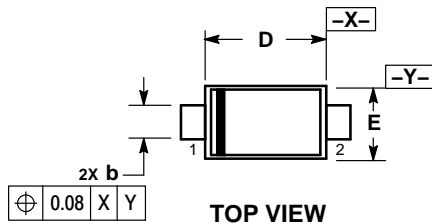


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ESD8351, SZESD8351

PACKAGE DIMENSIONS

SOD-923
CASE 514AB
ISSUE C

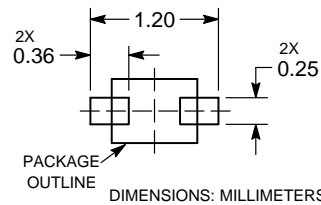


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
H _E	0.95	1.00	1.05	0.037	0.039	0.041
L	0.19 REF			0.007 REF		
L2	0.05	0.10	0.15	0.002	0.004	0.006

SOLDERING FOOTPRINT*



See Application Note AND8455/D for more mounting details

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.